TOSHIBA Intelligent Power Module Silicon N Channel IGBT

MIG75J101H

High Power Switching Applications Motor Control Applications

• Integrates inverter & control circuits (igbt drive units, protection units for over-current, under-voltage & over-temperature) in one package.

• The electrodes are isolated from case.

• High speed type IGBT : VCE (sat) = 2.5 V (Max.)

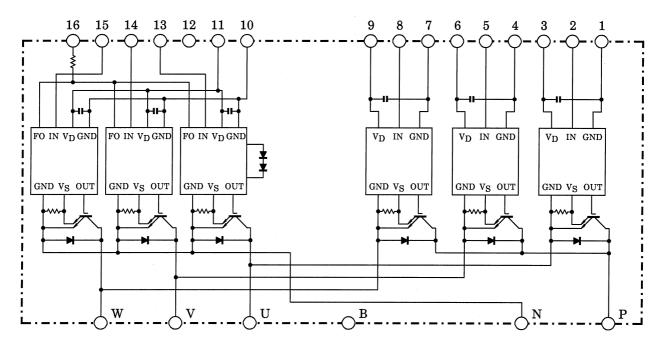
 t_{0} ff = 3.0 μs (Max.)

 $t_{rr}=0.30~\mu s~(Max.)$

• Outline : TOSHIBA 2-110A1A

● Weight : 520 g

Equivalent Circuit



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Maximum Ratings ($T_j = 25$ °C)

Stage	Characteristic	Condition	Symbol	Ratings	Unit
Inverter	Supply voltage	P-N power terminal	V _{CC}	450	V
	Collector-emitter voltage	_	V _{CES}	600	V
	Collector current	Tc = 25°C, DC	IC	75	Α
	Forward current	Tc = 25°C, DC	l _F	75	Α
	Collector power dissipation	Tc = 25°C	PC	235	W
	Junction temperature	_	Tj	150	°C
Control	Control supply voltage	V _D -GND terminal	V_{D}	20	V
	Input voltage	IN-GND terminal	V _{IN}	20	V
	Fault output voltage	FO-GND (L) terminal	V _{FO}	20	V
	Fault output current	FO sink current	I _{FO}	14	mA
Module	Operating temperature	_	TC	-20 ~ +100	°C
	Storage temperature range	_	T _{stg}	-40 ~ +125	°C
	Isolation voltage	AC 1 minute	V _{ISO}	2500	V
	Screw torque	M5	_	3	Nm

Electrical Characteristics ($T_j = 25$ °C)

a. Inverter Stage

Characteristic	Symbol	Test Condition		Min	Тур.	Max	Unit
Collector cut-off current	I _{CEX} V _{CEX} =	Vo=v = 600V	T _j = 25°C	_	_	1	mA
Collector cut-on current		1 ACEX = 000 A	T _j = 125°C		_	20	
Collector-emitter saturation voltage	V _{CE} (sat)	$V_D = 15 \text{ V}, I_C = 75 \text{ A}$ $V_{IN} = 15 \text{ V} \rightarrow 0 \text{ V}$	T _j = 25°C		2.0	2.5	V
Collector-entitler Saturation Voltage			T _j = 125°C		2.0	-	
Forward voltage	V _F	I _F = 75A		_	2.1	3.0	V
	t _{on}	V _{CC} = 300 V, I _C = 75 A		-	1.0	2.0	- - µs
Switching time	t _{off}	$V_D = 15 \text{ V}, V_{IN} = 15 \text{ V}$		1.2	3.0		
Switching time	t _f	Inductive load	(Note 1)	- 0.2	0.5		
	t _{rr}		(Note 1)	_	0.1	0.3	

b. Control Stage $(T_j = 25^{\circ}C)$

Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit	
Control circuit current	High side	I _{D (H)}	- V _D = 15 V	_	8	_	mA	
Control Circuit Current	Low side	I _{D (L)}		_	24	_		
Input-on signal voltage		V _{IN (on)}	V _D = 15 V, I _C = 75 mA	1.3	1.5	1.7	V	
Input-off signal voltage		V _{IN (off)}	V _D = 15 V, I _C = 75 mA	2.2	2.5	2.8	V	
Fault output current	Protection	I _{FO (on)}	- V _D = 15 V	8	10	12	mA	
	Normal	I _{FO (off)}		_	_	1		
Over current protection trip level	Inverter	ОС	V _D = 15 V, T _j = 125°C	105	150	_	Α	
Short circuit protection trip level	Inverter	SC	V _D = 15 V, T _j = 125°C	157	225	_	Α	
Over current cut-off time		t _{off (OC)}	V _D = 15 V	_	5	_	μs	
Over temperature	Trip level	ОТ	Case temperature	110	118	125	°C	
protection	Reset level	OTr		_	98	_		
Control supply under	Trip level	UV		11.0	12.0	12.5		
voltage protection	Reset level	UVr		_	12.5	_	V	
Fault output pulse width		t _{FO}	V _D = 15 V	1	2	3	ms	

^{*1:} Duty = 50%

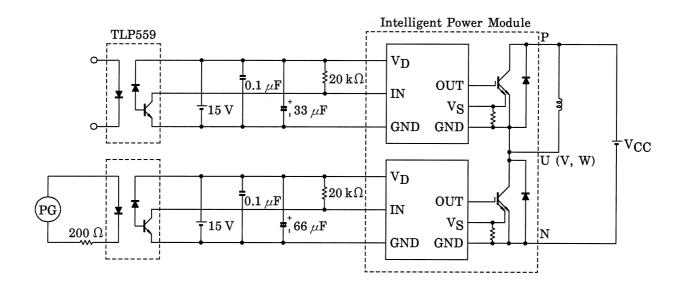
^{*2:} Duty = 50% (all elements) & fault output current (sink)

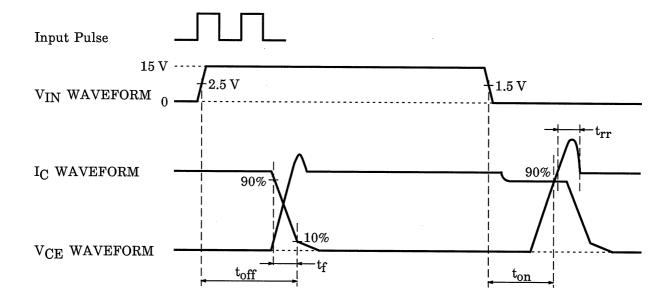


d. Thermal Resistance ($T_j = 25$ °C)

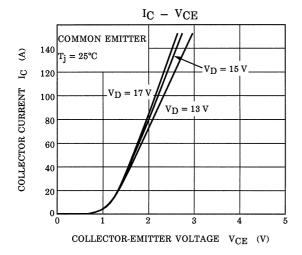
Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
	Du # >	Inverter IGBT stage	_	_	0.553	°C/W
Junction to case thermal resistance		Inverter FRD stage	-	_	1.000	
Junction to case thermal resistance	R _{th (j-c)}	_	_	_	_	
		_	_	_	_	
Case to fin thermal resistance	R _{th (c-f)}	Compound is applied	_	0.05	_	°C/W

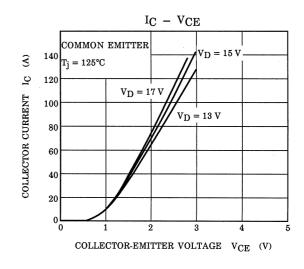
Note 1: Switching time test circuit & timing chart

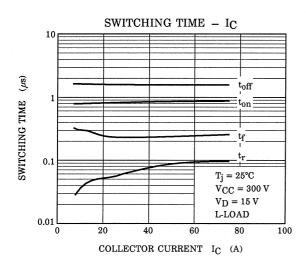


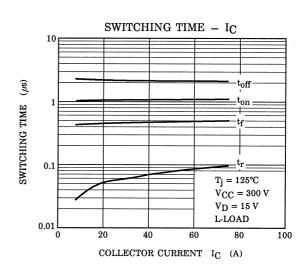


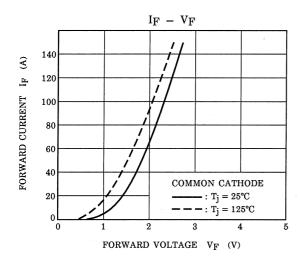
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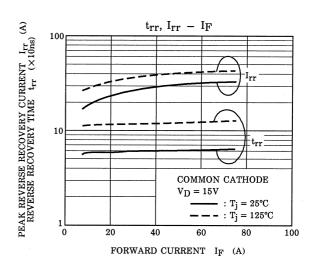




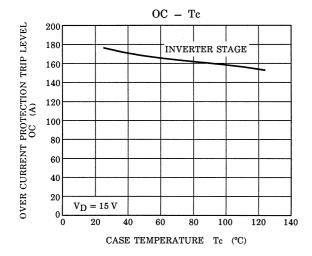


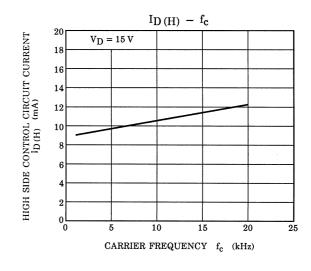


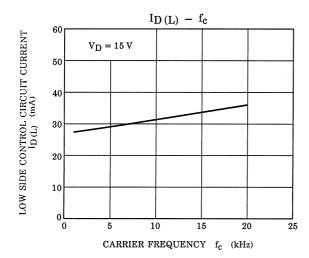


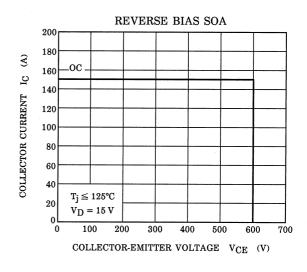


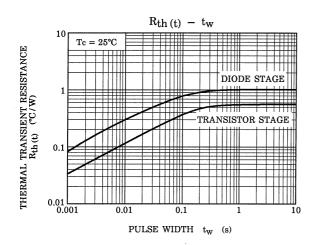
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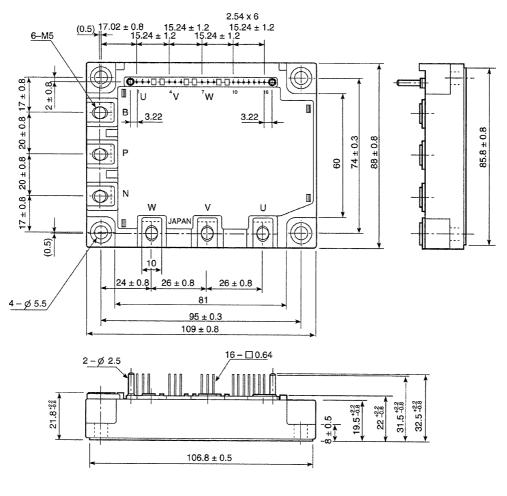






Package Dimensions

TOSHIBA 2-110A1A Unit: mm



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